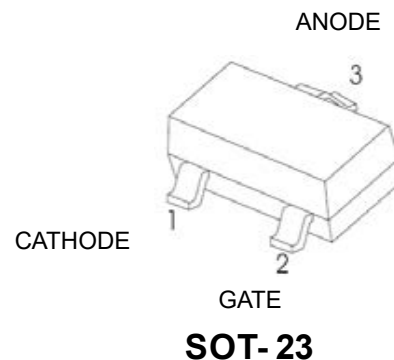


Silicon Planar PNP Thyristor

MAIN FEATURES

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current	0.6	A
V_{DRM}	Repetitive peak offstate voltage	600	V
T_j	Junction Temperature	-40~+125	°C
T_{stg}	Storage Temperature	-40~+150	°C



DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

FEATURES

- RMS on-state current to 0.6 A
- General purpose switching

APPLICATIONS

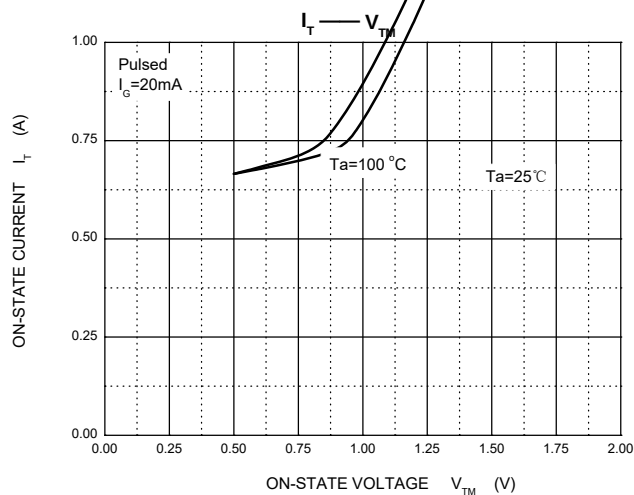
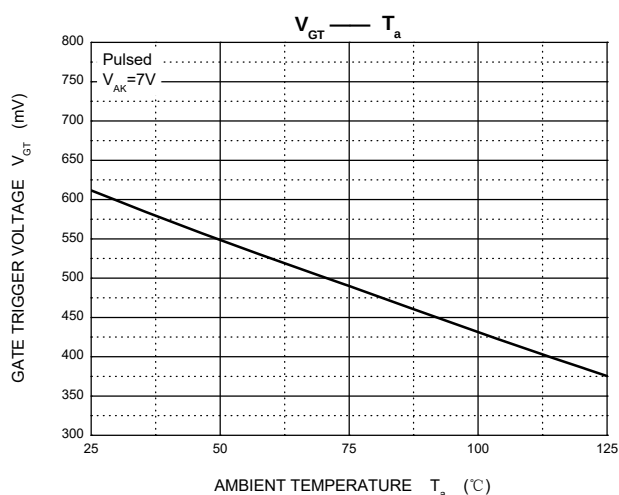
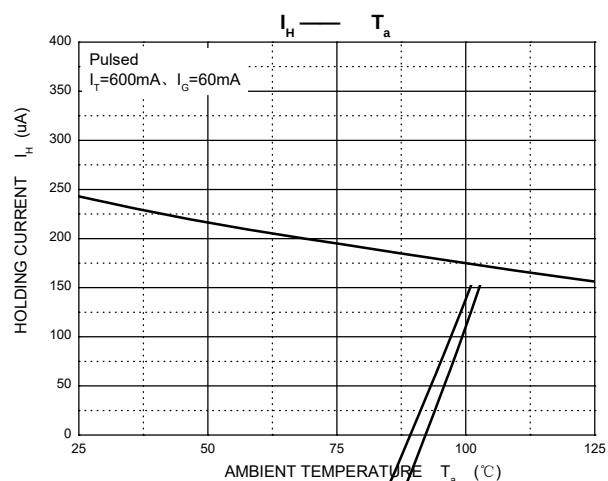
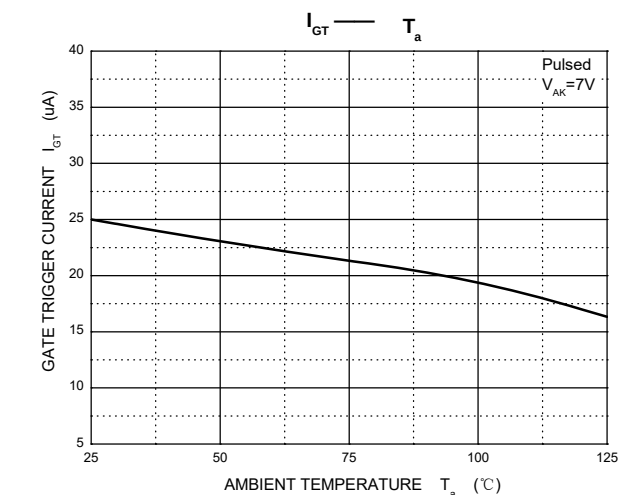
- General purpose switching
- Phase control applications
- Solid state relays

MARKING:606

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
On state voltage	V_{TM}	$I_{TM}=0.6\text{A}$		1.7	V
Gate trigger voltage	V_{GT}	$V_{AK}=7\text{V}$		0.8	V
Repetitive peak off-state voltage	V_{DRM}	$I_{DRM}=10\mu\text{A}$	600		V
Holding current	I_H	$I_T=600\text{mA}$, $I_G=60\text{mA}$		5	mA
Gate trigger current	I_{GT}	$V_{AK}=7\text{V}$	5	40	μA

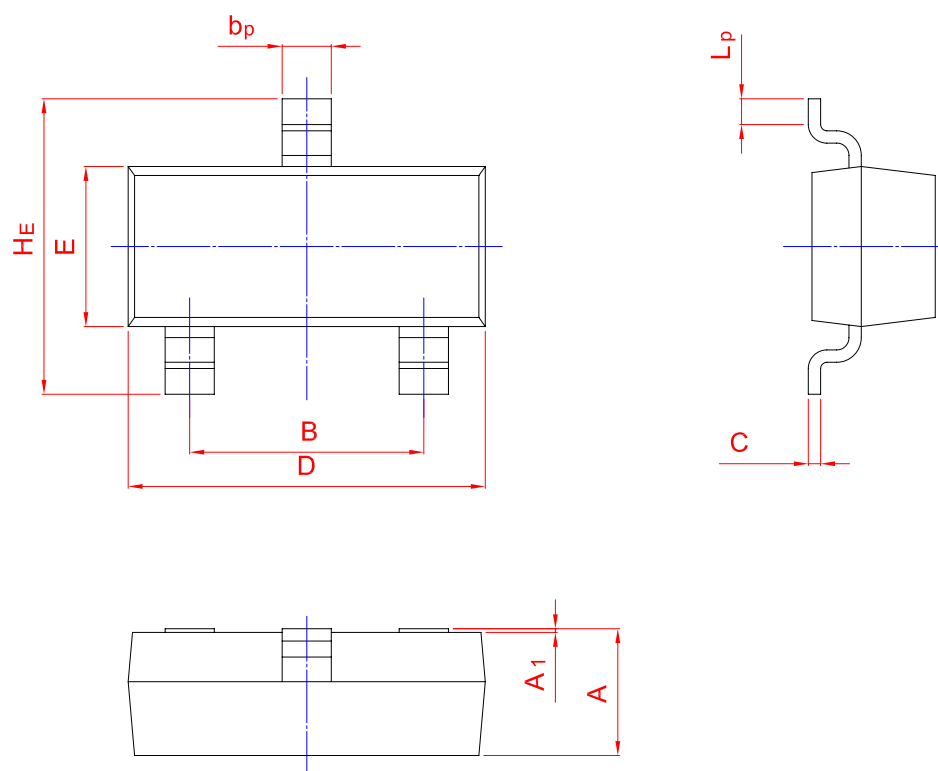
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20